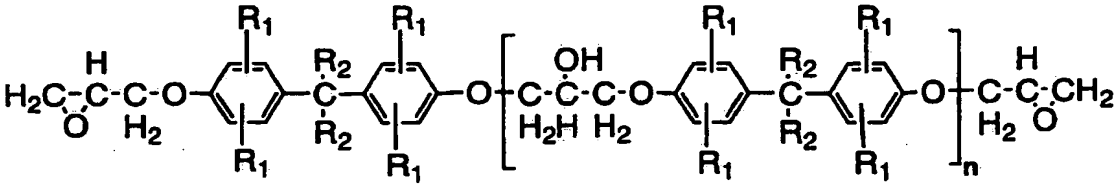
Claims

1. An epoxy resin for sealing photosemiconductor, comprising

(A) a bisphenol-type epoxy resin represented by the following formula (1)



(1)

(wherein, R_1s represent hydrogen atom, a C1 - C8 alkyl group, a halogen atom, which may be the same or different; R_2s represent hydrogen atom, a C1 - C5 alkyl group, a halogen-substituted (C1 - C5) alkyl group or phenyl group, which may be the same or different; n represents an integer), where the ratio of the total content of such bisphenol-type lower molecular epoxy resins with n = 0, 1 or 2 is 10% by weight or more based on the whole resin;

(B) a terpene backbone-containing polyvalent phenol curing agent prepared by adding two molecules of phenols to one molecule of a cyclic terpene compound;

(C) a curing-promoting agent;

(D) at least one resin selected from the group consisting of epoxy resins except for the component (A) and novolak resins as curing agents.

2. The epoxy resin composition for sealing

photosemiconductor according to claim 1 containing epoxy resins except for the component A, where the ratio of the total content of bisphenol-type lower molecular epoxy resins with n = 0, 1 or 2 in the formula (1) is 10% by weight or more based on the whole epoxy resin.

3. The epoxy resin composition for sealing photosemiconductor according to claim 1, where the ratio of the total content of the bisphenol-type lower molecular epoxy resins in the epoxy resin of the component (A) is 15 to 50% by weight based on the whole component (A).

4. The epoxy resin composition for sealing photosemiconductor according to claim 1 or 3 containing epoxy resins except for the epoxy resin of the component (A) as the component (D) at 20 to 90% by weight and the epoxy resin of the component (A) at 10 to 80%, by weight based on the whole epoxy resin.

5. The epoxy resin composition for sealing photosemiconductor according to claim 4, where the epoxy resins except for the component (A) are biphenyl backbone-containing phenol novolak resins.

6. The epoxy resin composition for sealing photosemiconductor according to claim 1, where the component (A) is bisphenol type-A and/or bisphenol type-F epoxy resin.

7. The epoxy resin composition for sealing photosemiconductor according to claim 1, where the terpene

backbone-containing polyvalent phenol curing agent as the component (B) is of a bifunctional type.

8. A photosemiconductor device sealed with a cured material of an epoxy resin composition according to any one of claims 1 to 7.

9. A method for producing sealed photosemiconductor device characterized by sealing an photosemiconductor device with an epoxy resin composition according to any one of claims 1 to 7.

10. The epoxy resin composition according to any one of claims 1 to 7, where the cured product of the resin composition has a glass transition temperature of 105°C or more and the ratio of the peeled area of the cured resin after absorption of moisture in the photosemiconductor device sealed with the said cured product is 60% or less.